

ABSTRACT

A base polymer having incorporated an ester group
5 having a fluorinated alicyclic unit is provided. A resist
composition comprising the polymer is sensitive to high-
energy radiation, and has excellent sensitivity at a
wavelength of less than 200 nm, significantly improved
transparency by virtue of the fluorinated alicyclic units
10 incorporated as well as satisfactory plasma etching
resistance. The resist composition has a low absorption at
the exposure wavelength of a F₂ laser and is ideal as a
micropatterning material in VLSI fabrication.